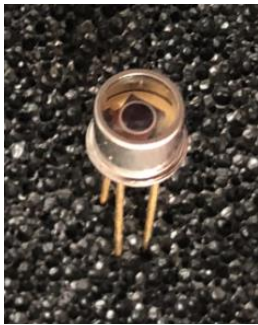


IR Sensitive Silicon Photodiode



Description

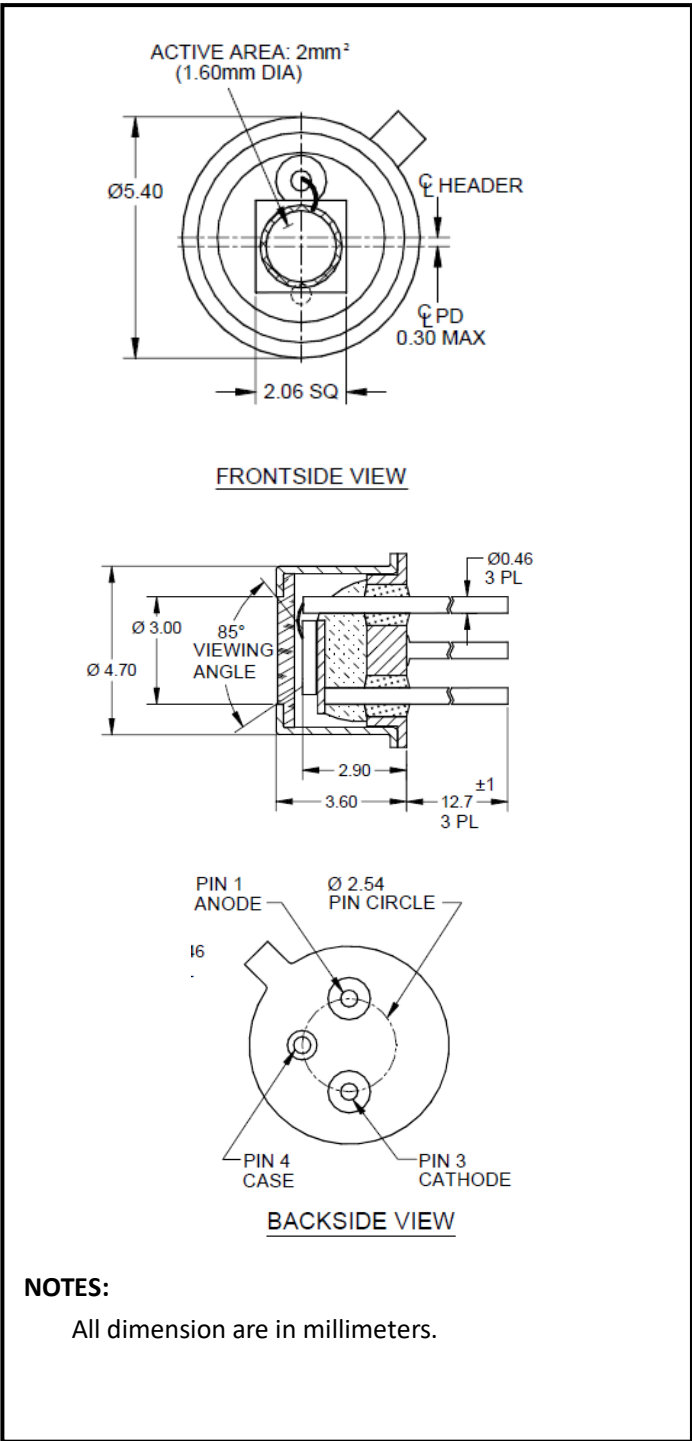
The OSD002-IT is high-output, high sensitivity silicon Photodiode hermetically packaged in TO52 package with A clear borosilicate glass window cap.

Features

- * High speed response
- * Wide angular response
- * High reliability in demanding environments
- * Operating temperature is from -40 to +80°C
- * Storage temperature is from -40 to +100°C

Applications

- * Analytical instruments
- * Precision photometry
- * Fluorescence detector
- * IR/ Laser light Monitoring



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

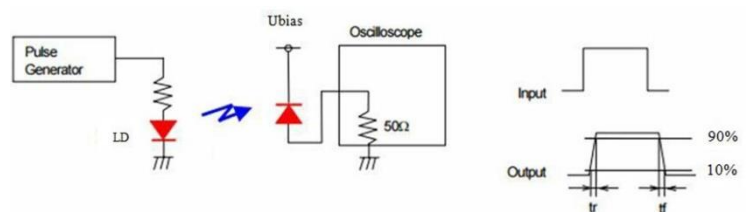
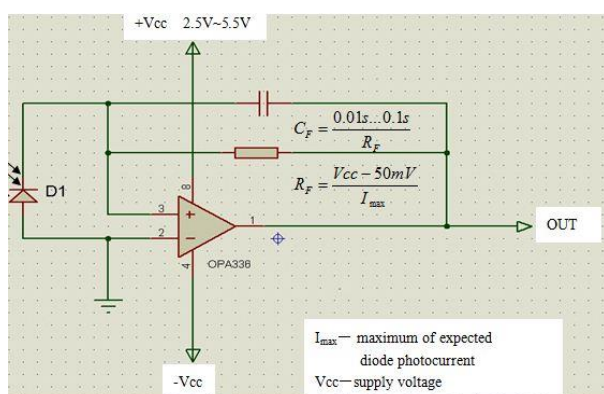
Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Active area	A			Φ 1.60		mm
				2		mm ²
Dark current	I _D	V _R =10mV		100		pA
		V _R =10V		10		
Rise time**	t _R	V _R =10V;λ=635nm;R _L =50Ω, f=1MHz		12		ns
Tempcoefficient of I _D	T _{CD}			0.18		times/°C
Reverse breakdown voltage	V _{(BR)R}	I _R =100μA E _v =0lx		50		V
Junction Capacitance	C _J	E _v =0lx V _R =0V f=1MHz		82		pF
		E _v =0lx V _R =10V f=1MHz		13		
Photo sensitivity	S _R	650nm		0.38		A/W
		940nm		0.64		
Spectral Application Range	λ _{range}		400		1100	nm
Spectral Response-Peak	λ _p			940		nm
Shunt resistance	R _{sh}	V _R =10mV		0.1		GΩ
Rsh Temperature Coefficient	TC Rsh			0.18		%/°C
Angular Resp 50% Resp Pt	θ _{1/2}			±55		Degrees
Noise Equivalent Power	NEP	V _R =10V λ=940nm		0.9×10 ⁻¹⁴		W/Hz ^{1/2}
Specific Detectivity	D*	V _R =10V λ=940nm		1.1×10 ¹³		cm(Hz/W) ^{1/2}

* E_v: Illuminance by CIE standard light source A (tungsten lamp)

■ Typical application circuit

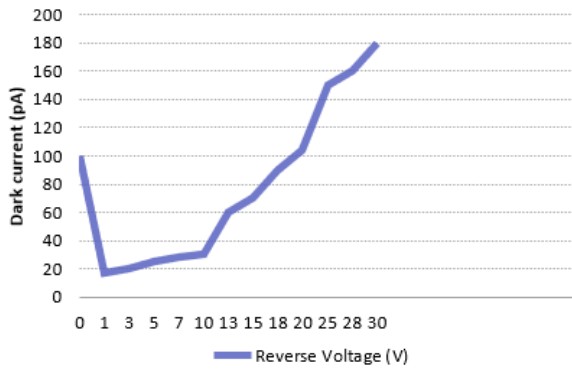
** Response time measurement Circuit:



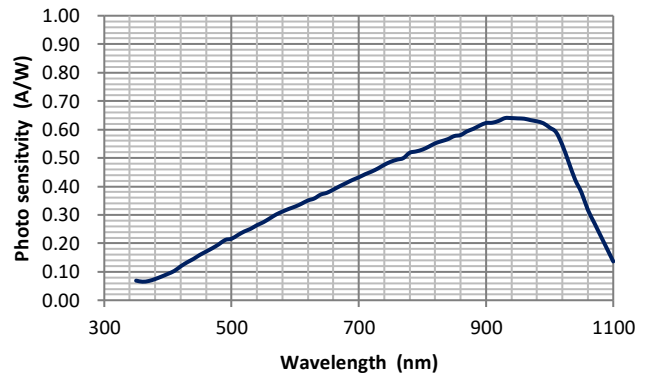
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■ Dark current vs. reverse voltage

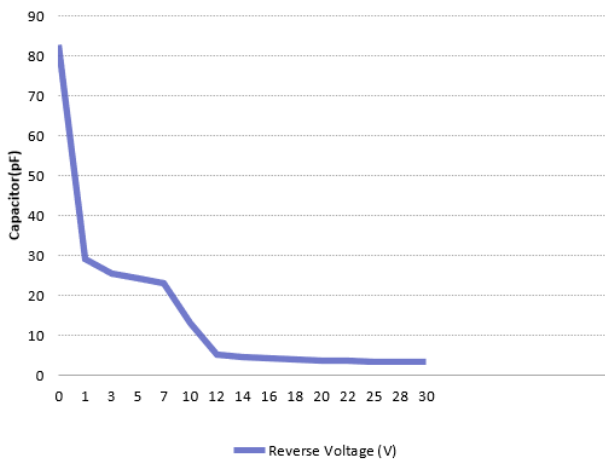


■ Spectral response

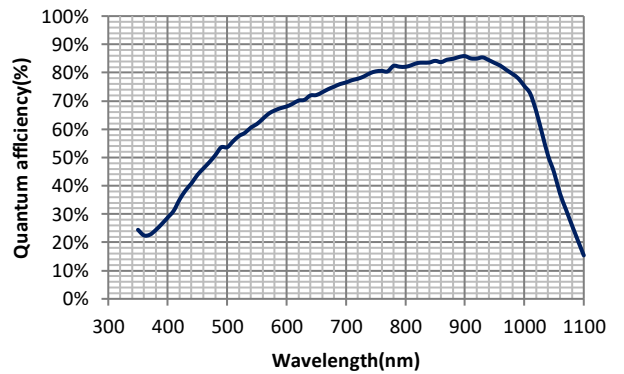


■ Relative Junction Capacitance

VS. Voltage



■ Quantum efficiency



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